

Amendments to the Specification.

Please amend the paragraph bridging columns 5 and 6 to read as follows:

After the deposition of the barrier layer, a seed layer 13 may be deposited over the barrier layer 11 including on the walls and bottom of the recess(es). The preferred seed layer is copper, which can be deposited by sputtering or evaporation and preferably by sputtering. The copper may be sputtered employing temperatures of less than about 150.degree. C, preferably less than about 100°C, such as about 100°C to about -10°C. The sputtering may be carried out in the absence of an anneal. The sputtering is typically carried out to provide a seed layer of about 100 Å to about 2000 Å and preferably about 400 Å to about 1000 Å. Also, the copper seed layer may be deposited by CVD methods or by electroless plating method or by an electrolytic plating method.